

TENTATIVE

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCXH162373FT

Low-Voltage 16-Bit D-Type Latch with Bushold

The TC74VCXH162373FT is a high-performance CMOS 16-bit D-type latch. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

This 16-bit D-type latch is controlled by a latch enable input (LE) and a output enable input (\overline{OE}) which are common to each byte. It can be used as two 8-bit latches or one 16-bit latch. When the \overline{OE} input is high, the outputs are in a high-impedance state.

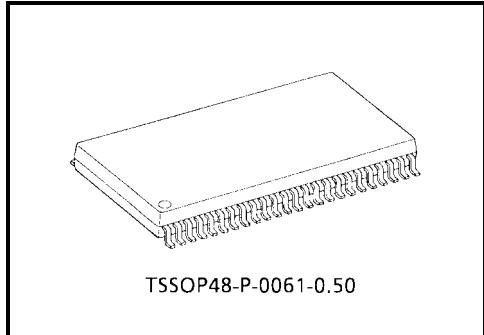
The $26\text{-}\Omega$ series resistor helps reducing output overshoot and undershoot without external resistor.

The D data inputs include active bushold circuitry, eliminating the need for external pull-up resistors to hold unused or floating data inputs at a valid logic level.

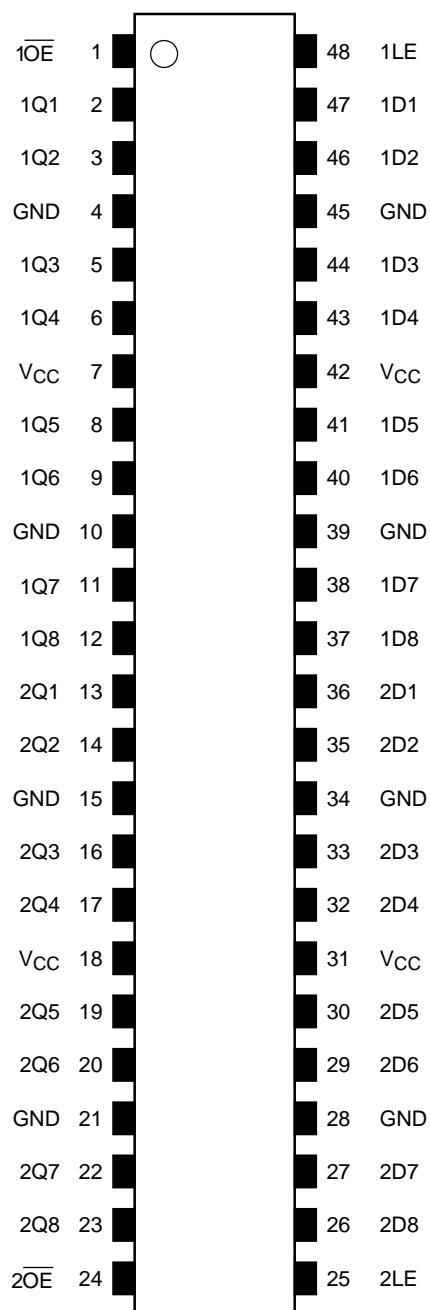
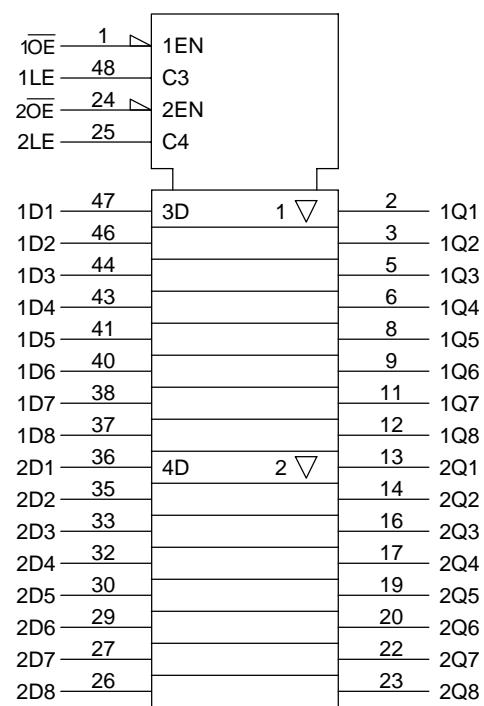
All inputs are equipped with protection circuits against static discharge.

Features

- 26- Ω series resistors on outputs
- Low-voltage operation: $V_{CC} = 1.8$ to 3.6 V
- Bushold on data inputs eliminating the need for external pull-up/pull-down resistors
- High-speed operation: $t_{pd} = 3.3$ ns (max) ($V_{CC} = 3.0$ to 3.6 V)
 - : $t_{pd} = 4.5$ ns (max) ($V_{CC} = 2.3$ to 2.7 V)
 - : $t_{pd} = 5.8$ ns (max) ($V_{CC} = 1.8$ V)
- Output current: $I_{OH}/I_{OL} = \pm 12$ mA (min) ($V_{CC} = 3.0$ V)
 - : $I_{OH}/I_{OL} = \pm 8$ mA (min) ($V_{CC} = 2.3$ V)
 - : $I_{OH}/I_{OL} = \pm 4$ mA (min) ($V_{CC} = 1.8$ V)
- Latch-up performance: ± 300 mA
- ESD performance: Machine model $> \pm 200$ V
 - : Human body model $> \pm 2000$ V
- Package: TSSOP (thin shrink small outline package)
- 3.6-V tolerant function and power-down protection control inputs and outputs



Weight: 0.25 g (typ.)

Pin Assignment (top view)**IEC Logic Symbol**

Truth Table

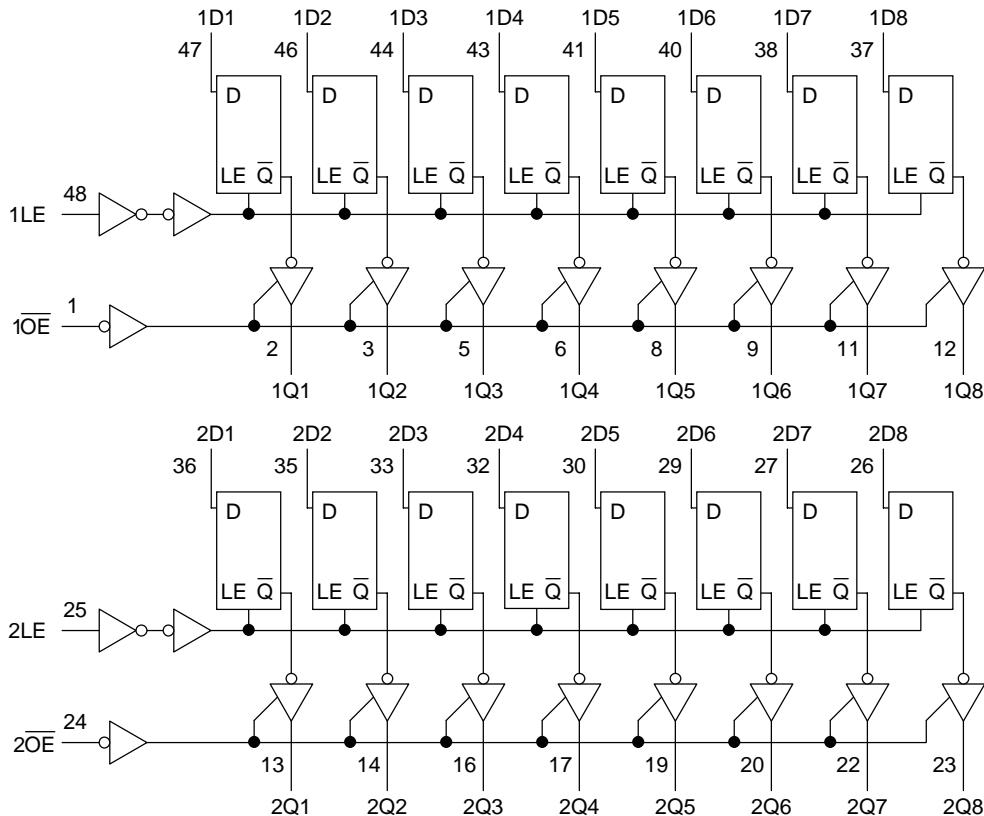
Inputs			Outputs
$\bar{1OE}$	1LE	1D1-1D8	1Q1-1Q8
H	X	X	Z
L	L	X	Qn
L	H	L	L
L	H	H	H

Inputs			Outputs
$\bar{2OE}$	2LE	2D1-2D8	2Q1-2Q8
H	X	X	Z
L	L	X	Qn
L	H	L	L
L	H	H	H

X: Don't care

Z: High impedance

Qn: Q outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram

Maximum Ratings

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 4.6	V
DC input voltage (An)	V _{IN}	-0.5 to 4.6	V
		-0.5 to V _{CC} + 0.5	
DC output voltage	V _{OUT}	-0.5 to 4.6 (Note 1)	V
		-0.5 to V _{CC} + 0.5 (Note 2)	
Input diode current	I _{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note 3)	mA
Output current	I _{OUT}	±50	mA
Power dissipation	P _D	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: OFF state

Note 2: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 3: V_{OUT} < GND, V_{OUT} > V_{CC}

Recommended Operating Range (Note 4)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	1.8 to 3.6	V
		1.2 to 3.6 (Note 5)	
(OE, LE) (An)	V _{IN}	-0.3 to 3.6	V
		0 to V _{CC}	
Output voltage	V _{OUT}	0 to 3.6 (Note 6)	V
		0 to V _{CC} (Note 7)	
Output current	I _{OH} /I _{OL}	±12 (Note 8)	mA
		±8 (Note 9)	
		±4 (Note 10)	
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	d _t /d _v	0 to 10 (Note 11)	ns/V

Note 4: Floating or unused control inputs must be held high or low.

Note 5: Data retention

Note 6: OFF state

Note 7: High or low state

Note 8: V_{CC} = 3.0 to 3.6 V

Note 9: V_{CC} = 2.3 to 2.7 V

Note 10: V_{CC} = 1.8 V

Note 11: V_{IN} = 0.8 to 2.0 V, V_{CC} = 3.0 V

Electrical Characteristics**DC Characteristics (Ta = -40 to 85°C, 2.7 V < V_{CC} ≤ 3.6 V)**

Characteristics		Symbol	Test Condition		V _{CC} (V)	Min	Max	Unit
Input voltage	H-level	V _{IH}	—		2.7 to 3.6	2.0	—	V
	L-level	V _{IL}	—		2.7 to 3.6	—	0.8	
Output voltage	H-level	V _{OH}	V _{IN} = V _{IH} or V _{IL}	I _{OH} = -100 μA	2.7 to 3.6	V _{CC} - 0.2	—	V
				I _{OH} = -6 mA	2.7	2.2	—	
				I _{OH} = -8 mA	3.0	2.4	—	
				I _{OH} = -12 mA	3.0	2.2	—	
	L-level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 100 μA	2.7 to 3.6	—	0.2	
				I _{OL} = 6 mA	2.7	—	0.4	
				I _{OL} = 8 mA	3.0	—	0.5	
				I _{OL} = 12 mA	3.0	—	0.8	
Input leakage current	(OE, LE)	I _{IN}	V _{IN} = 0 to 3.6 V		2.7 to 3.6	—	±5.0	μA
	(An)		V _{IN} = V _{CC} or GND		2.7 to 3.6	—	±5.0	
Bushold input minimum drive hold current		I _I (HOLD)	V _{IN} = 0.8 V		3.0	75	—	μA
			V _{IN} = 2.0 V		3.0	-75	—	
Bushold input over-drive current to change state		I _I (OD)	(Note 12)		3.6	—	450	μA
			(Note 13)		3.6	—	-450	
3-state output OFF state current		I _{OZ}	V _{IN} = V _{IH} or V _{IL} V _{OUT} = 0 to 3.6 V		2.7 to 3.6	—	±10.0	μA
Power-off leakage current		I _{OFF}	V _{OUT} = 0 to 3.6 V		0	—	10.0	μA
Quiescent supply current		I _{CC}	V _{IN} = V _{CC} or GND		2.7 to 3.6	—	20.0	μA
			V _{CC} ≤ V _{OUT} ≤ 3.6 V (Note 14)		2.7 to 3.6	—	±20.0	
Increase in I _{CC} per input		ΔI _{CC}	V _{IH} = V _{CC} - 0.6 V		2.7 to 3.6	—	750	μA

Note 12: An external driver must source at least the specified current to switch LOW-to-HIGH.

Note 13: An external driver must sink at least the specified current to switch HIGH-to-LOW.

Note 14: Outputs high impedance only.

DC Characteristics ($T_a = -40$ to 85°C , $2.3 \text{ V} \leq V_{CC} \leq 2.7 \text{ V}$)

Characteristics		Symbol	Test Condition	$V_{CC} (\text{V})$	Min	Max	Unit
Input voltage	H-level						
	L-level	V_{IL}	—	2.3 to 2.7	—	0.7	
Output voltage	H-level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$	2.3 to 2.7	$V_{CC} - 0.2$	—
				$I_{OH} = -4 \text{ mA}$	2.3	2.0	—
				$I_{OH} = -6 \text{ mA}$	2.3	1.8	—
				$I_{OH} = -8 \text{ mA}$	2.3	1.7	—
	L-level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$	2.3 to 2.7	—	0.2
				$I_{OL} = 6 \text{ mA}$	2.3	—	0.4
				$I_{OL} = 8 \text{ mA}$	2.3	—	0.6
Input leakage current	(\bar{OE} , LE)	I_{IN}	$V_{IN} = 0$ to 3.6 V	2.3 to 2.7	—	± 5.0	μA
	(An)		$V_{IN} = V_{CC}$ or GND	2.3 to 2.7	—	± 5.0	
Bushold input minimum drive hold current	I_I (HOLD)		$V_{IN} = 0.7 \text{ V}$	2.3	45	—	μA
			$V_{IN} = 1.6 \text{ V}$	2.3	-45	—	
Bushold input over-drive current to change state	I_I (OD)		(Note 12)	2.7	—	300	μA
			(Note 13)	2.7	—	-300	
3-state output OFF state current	I_{OZ}		$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V	2.3 to 2.7	—	± 10.0	μA
Power-off leakage current	I_{OFF}		$V_{OUT} = 0$ to 3.6 V	0	—	10.0	μA
Quiescent supply current	I_{CC}		$V_{IN} = V_{CC}$ or GND	2.3 to 2.7	—	20.0	μA
			$V_{CC} \leq V_{OUT} \leq 3.6 \text{ V}$	(Note 14)	2.3 to 2.7	—	

Note 12: An external driver must source at least the specified current to switch LOW-to-HIGH.

Note 13: An external driver must sink at least the specified current to switch HIGH-to-LOW.

Note 14: Outputs high impedance only.

DC Characteristics ($T_a = -40$ to 85°C , $1.8 \text{ V} \leq V_{CC} < 2.3 \text{ V}$)

Characteristics		Symbol	Test Condition		$V_{CC} (\text{V})$	Min	Max	Unit	
Input voltage	H-level	V_{IH}	—			1.8 to 2.3	$0.7 \times V_{CC}$	—	
	L-level	V_{IL}	—			1.8 to 2.3	—	$0.2 \times V_{CC}$	
Output voltage	H-level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$	1.8	$V_{CC} - 0.2$	—	V	
		V_{OL}		$I_{OH} = -4 \text{ mA}$	1.8	1.4	—		
		V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$	1.8	—	0.2		
				$I_{OL} = 4 \text{ mA}$	1.8	—	0.3		
Input leakage current	(\overline{OE})	I_{IN}	$V_{IN} = 0$ to 3.6 V		1.8	—	± 5.0	μA	
	(An)		$V_{IN} = V_{CC}$ or GND		1.8	—	± 5.0		
Bushold input minimum drive hold current		$I_I (\text{HOLD})$	$V_{IN} = 0.36 \text{ V}$		1.8	25	—	μA	
			$V_{IN} = 1.26 \text{ V}$		1.8	-25	—		
Bushold input over-drive current to change state		$I_I (\text{OD})$	(Note 12)		1.8	—	200	μA	
			(Note 13)		1.8	—	-200		
3-state output OFF state current		I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V		1.8	—	± 10.0	μA	
Power-off leakage current		I_{OFF}	$V_{OUT} = 0$ to 3.6 V		0	—	10.0	μA	
Quiescent supply current		I_{CC}	$V_{IN} = V_{CC}$ or GND		1.8	—	20.0	μA	
			$V_{CC} \leq V_{OUT} \leq 3.6 \text{ V}$		(Note 14)	1.8	—		

Note 12: An external driver must source at least the specified current to switch LOW-to-HIGH.

Note 13: An external driver must sink at least the specified current to switch HIGH-to-LOW.

Note 14: Outputs high impedance only.

AC Characteristics ($T_a = -40$ to 85°C , input: $t_r = t_f = 2.0$ ns, $C_L = 30$ pF, $R_L = 500 \Omega$)

Characteristics	Symbol	Test Condition	VCC (V)	Min	Max	Unit
Propagation delay time (D-Q)	t_{pLH} t_{pHL}	Figure 1, Figure 2	1.8	1.5	5.8	ns
			2.5 ± 0.2	1.0	4.5	
			3.3 ± 0.3	0.8	3.3	
Propagation delay time (LE-Q)	t_{pLH} t_{pHL}	Figure 1, Figure 2	1.8	1.5	6.2	ns
			2.5 ± 0.2	1.0	4.9	
			3.3 ± 0.3	0.8	3.6	
3-state output enable time	t_{pZL} t_{pZH}	Figure 1, Figure 3	1.8	1.5	7.6	ns
			2.5 ± 0.2	1.0	5.4	
			3.3 ± 0.3	0.8	3.9	
3-state output disable time	t_{pLZ} t_{pHZ}	Figure 1, Figure 3	1.8	1.5	5.3	ns
			2.5 ± 0.2	1.0	4.4	
			3.3 ± 0.3	0.8	4.0	
Minimum pulse width (LE)	t_w (H)	Figure 1, Figure 2	1.8	3.0	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum set-up time	t_s	Figure 1, Figure 2	1.8	2.5	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum hold time	t_h	Figure 1, Figure 2	1.8	1.0	—	ns
			2.5 ± 0.2	1.0	—	
			3.3 ± 0.3	1.0	—	
Output to output skew	t_{osLH} t_{osHL}	(Note 15)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

Note 15: Parameter guaranteed by design.

$$(tosLH = |t_{pLHm} - t_{pLHn}|, tosHL = |t_{pHLm} - t_{pHLn}|)$$

Dynamic Switching Characteristics (Ta = 25°C, input: t_r = t_f = 2.0 ns, C_L = 30 pF)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V _{OL}	V _{O LP}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 16)	1.8	0.15	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 16)	2.5	0.25	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 16)	3.3	0.35	
Quiet output minimum dynamic V _{OL}	V _{O LV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 16)	1.8	-0.15	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 16)	2.5	-0.25	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 16)	3.3	-0.35	
Quiet output minimum dynamic V _{OH}	V _{O HV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note 16)	1.8	1.55	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note 16)	2.5	2.05	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note 16)	3.3	2.65	

Note 16: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Input capacitance	C _{IN}	—	1.8, 2.5, 3.3	6	pF
Output capacitance	C _O	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Note 17)	1.8, 2.5, 3.3	20	pF

Note 17: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC} (\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/16 \text{ (per bit)}$$

AC Test Circuit

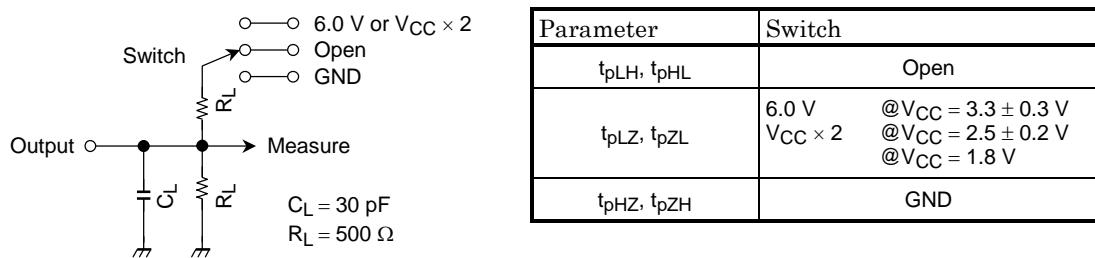
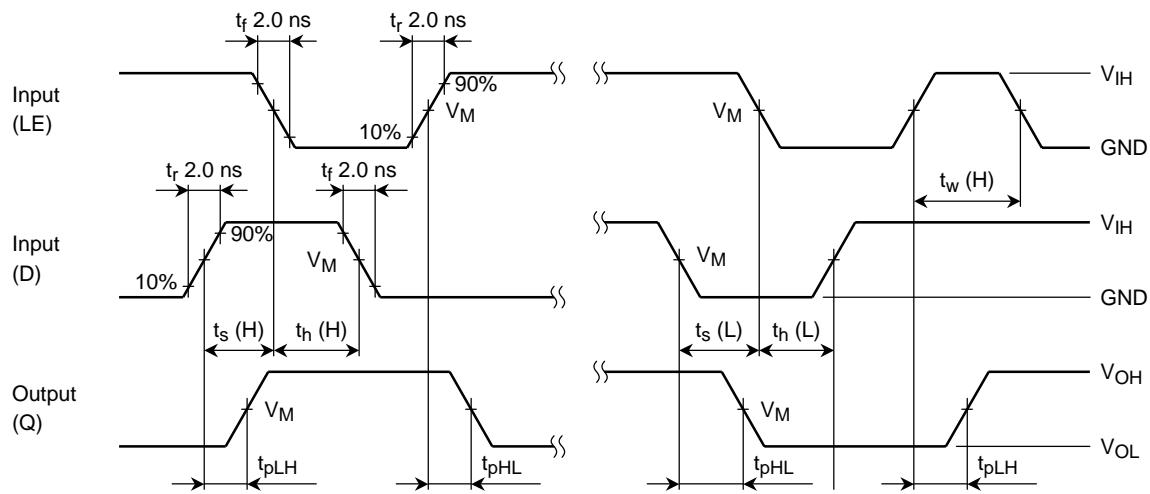


Figure 1

AC Waveform

Figure 2 $t_{pLH}, t_{pHL}, t_w, t_s, t_h$

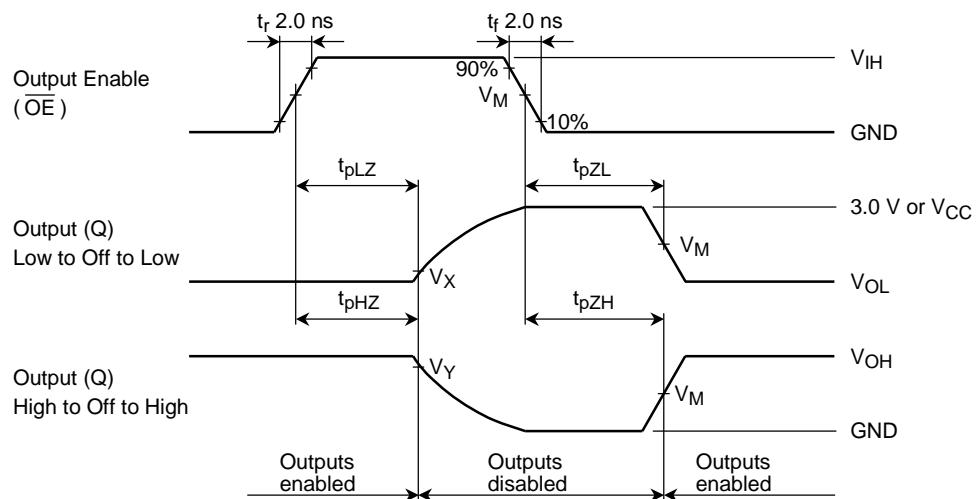


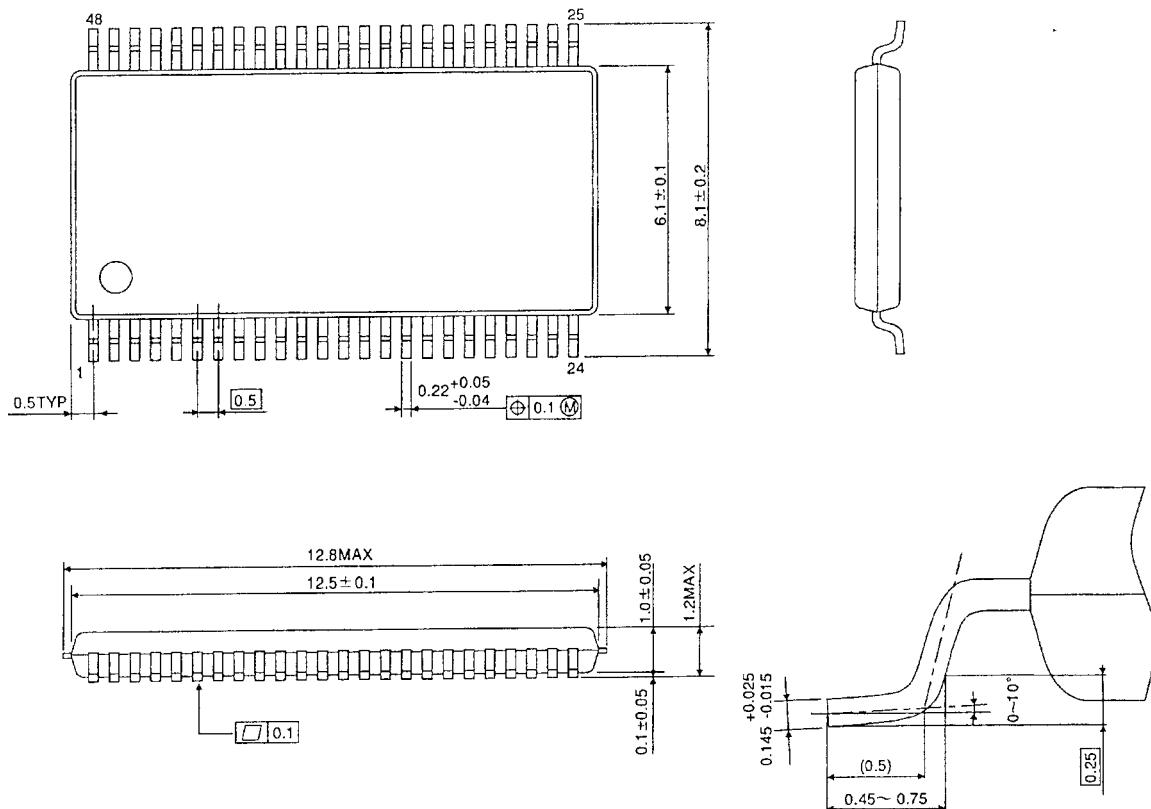
Figure 3 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

Symbol	V _{CC}		
	$3.3 \pm 0.3\text{ V}$	$2.5 \pm 0.2\text{ V}$	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$
V_X	$V_{OL} + 0.3\text{ V}$	$V_{OL} + 0.15\text{ V}$	$V_{OL} + 0.15\text{ V}$
V_Y	$V_{OH} - 0.3\text{ V}$	$V_{OH} - 0.15\text{ V}$	$V_{OH} - 0.15\text{ V}$

Package Dimensions

TSSOP48-P-0061-0.50

Unit : mm



Weight: 0.25 g (typ.)

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